



Toshiro Hiramoto

Toshiro Hiramoto received B.S., M.S., and Ph.D degrees in electronic engineering from the University of Tokyo in 1984, 1986, and 1989, respectively. In 1989, he joined Device Development Center, Hitachi Ltd., Ome, Japan. In 1994, he joined Institute of Industrial Science, University of Tokyo, Japan, as an Associate Professor and has been a Professor since 2002. His research interests include low power and low voltage design of advanced CMOS devices, variability in scaled CMOS, quantum effects in nano-scale MOSFETs, silicon nanowire transistors, and silicon single electron transistors.

Dr. Hiramoto is a member of IEEE, IEICE, and Japan Society of Applied Physics. He has served on Program Committee of Symposium on VLSI Technology since 2001. He also served on Program Subcommittee on Integrated Circuits of IEEE International Electron Devices Meeting (IEDM) in 1993, 1994 and Program Subcommittee on CMOS Devices of IEDM in 2003, 2004. He was the Subcommittee Chair of CMOS Devices of IEDM in 2005 and was the Asian Arrangement Co-Chair of IEDM in 2006 and 2007. He is the Publications Chair of IEDM in 2008 and the Emerging Technologies Chair of IEDM in 2009.